P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 30	0.016 at V_{GS} = - 10 V	- 10.6
	0.026 at V_{GS} = - 4.5 V	- 8.3

FEATURES

- TrenchFET® Power MOSFET
- ESD Protected: 2500 V

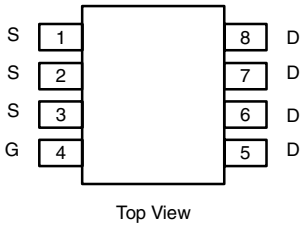
Pb-free Available

RoHS* COMPLIANT

APPLICATIONS

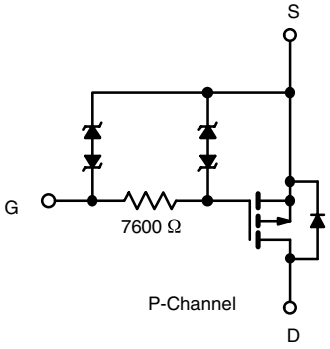
- Battery and Load Switching
  - Notebook

SO-8



Top View

Ordering Information: Si4441EDY-T1
Si4441EDY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 secs**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	- 30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 10.6	- 8.1	A
	T_A = 70 °C		- 8.5	- 6.5	
Pulsed Drain Current		I_{DM}	- 40		
Continuous Source Current (Diode Conduction)[a]		I_S	- 2.1	- 1.3	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2.5	1.5	W
	T_A = 70 °C		1.6	0.9	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a]	t ≤ 10 sec	R_{thJA}	37	50	°C/W
	Steady State		70	85	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	20	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

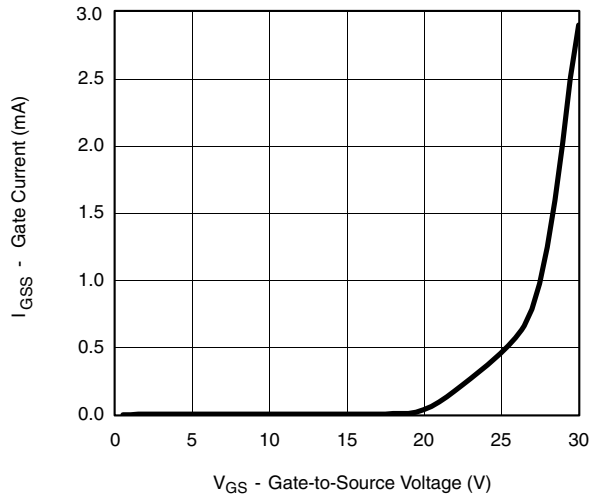
* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = - 250$ µA	- 1.0		- 3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 10$ V			± 20	µA
		$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			± 1	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = - 30$ V, $V_{GS} = 0$ V			- 1	µA
		$V_{DS} = - 30$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq - 5$ V, $V_{GS} = - 10$ V	- 40			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	$V_{GS} = - 10$ V, $I_D = - 10.6$ A		0.013	0.016	Ω
		$V_{GS} = - 4.5$ V, $I_D = - 8.3$ A		0.020	0.026	
Forward Transconductance[a]	g_{fs}	$V_{DS} = - 15$ V, $I_D = - 10.6$ A		43		S
Diode Forward Voltage[a]	V_{SD}	$I_S = - 2.1$ A, $V_{GS} = 0$ V		- 0.8	- 1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	$V_{DS} = - 15$ V, $V_{GS} = - 10$ V, $I_D = - 10.6$ A		45.5	70	nC
Gate-Source Charge	Q_{gs}			6.5		
Gate-Drain Charge	Q_{gd}			12.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = - 15$ V, $R_L = 15$ Ω $I_D \cong - 1$ A, $V_{GEN} = - 10$ V, $R_G = 6$ Ω		5	8	ns
Rise Time	t_r			11	20	
Turn-Off Delay Time	$t_{d(off)}$			45	70	
Fall Time	t_f			35	55	

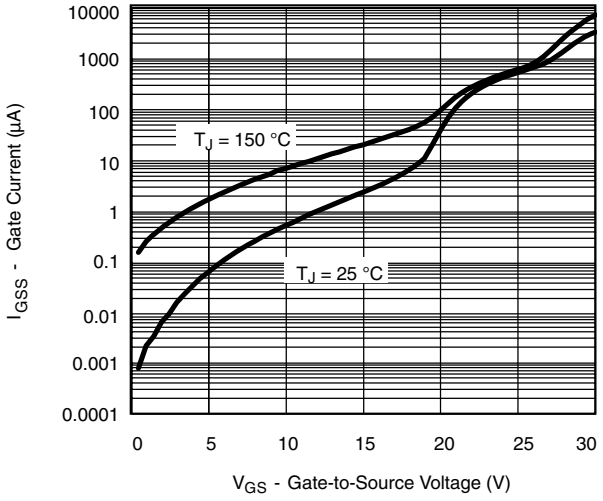
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless noted

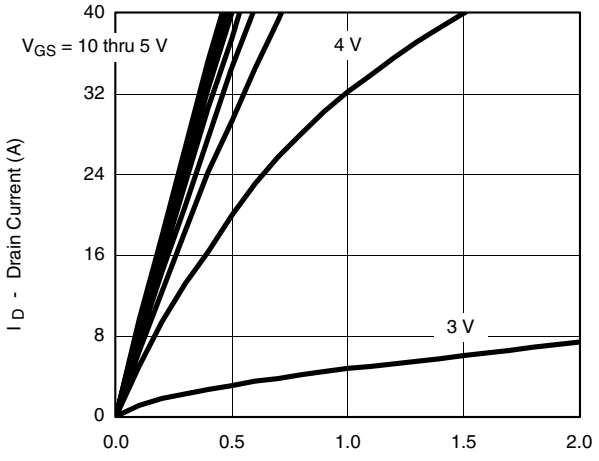


Gate-Current vs. Gate-Source Voltage

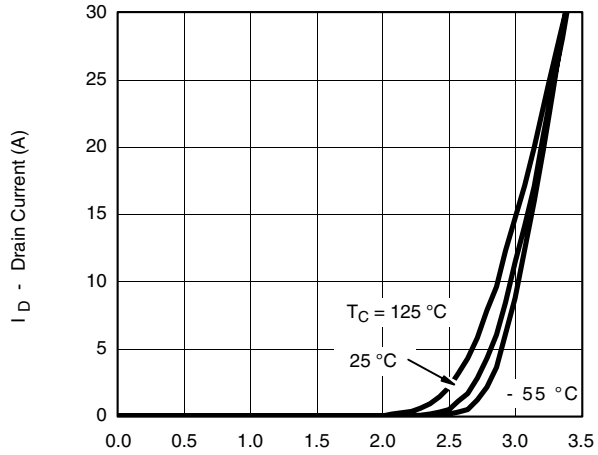


Gate Current vs. Gate-Source Voltage

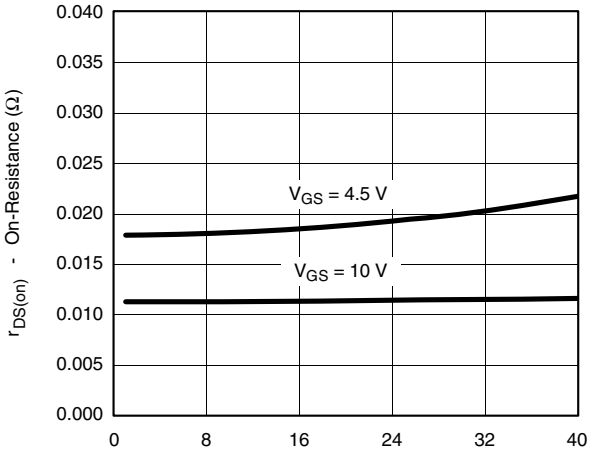
TYPICAL CHARACTERISTICS 25 °C, unless noted



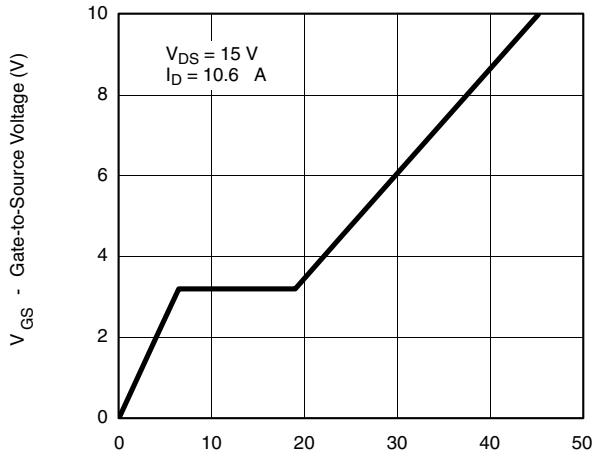
Output Characteristics



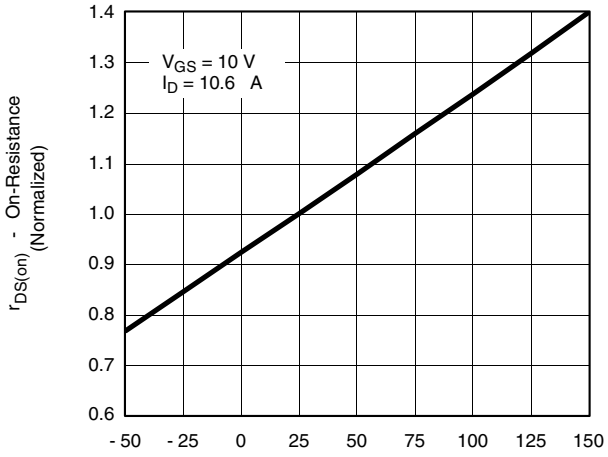
Transfer Characteristics



On-Resistance vs. Drain Current

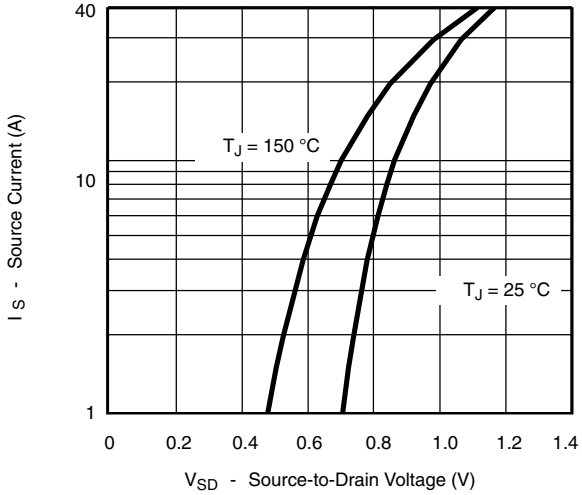


Gate Charge

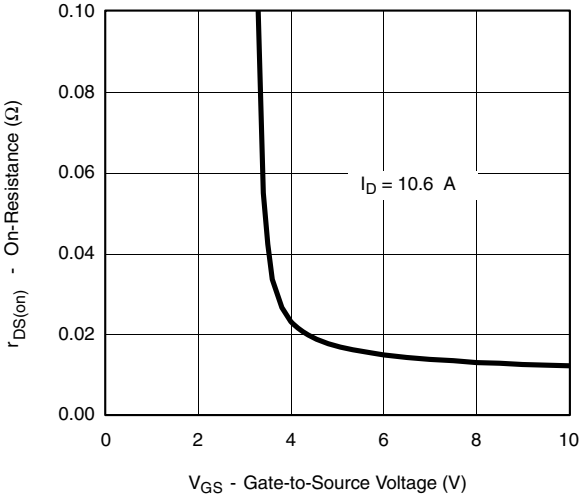


On-Resistance vs. Junction Temperature

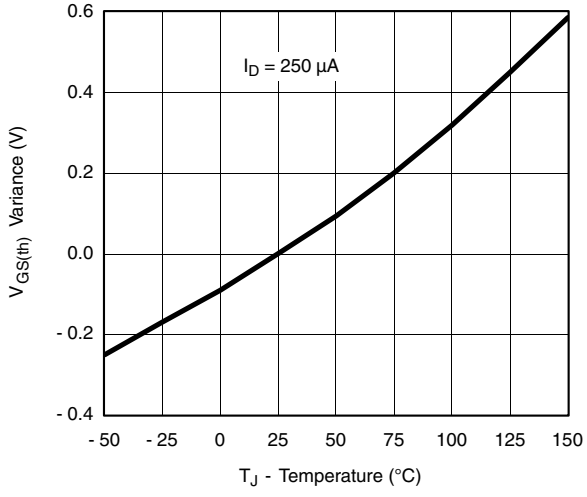
TYPICAL CHARACTERISTICS 25 °C, unless noted



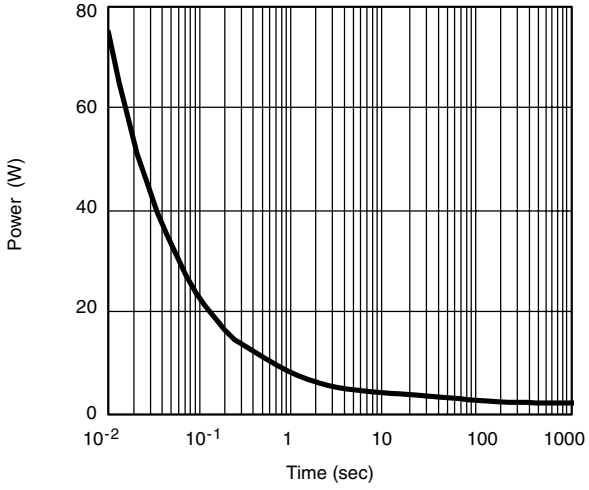
Source-Drain Diode Forward Voltage



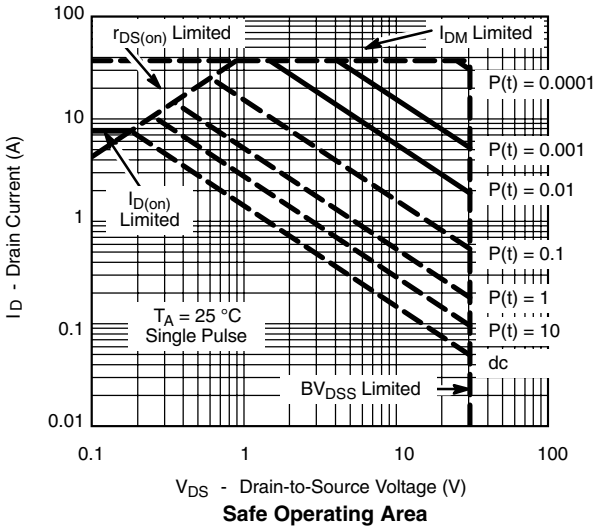
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

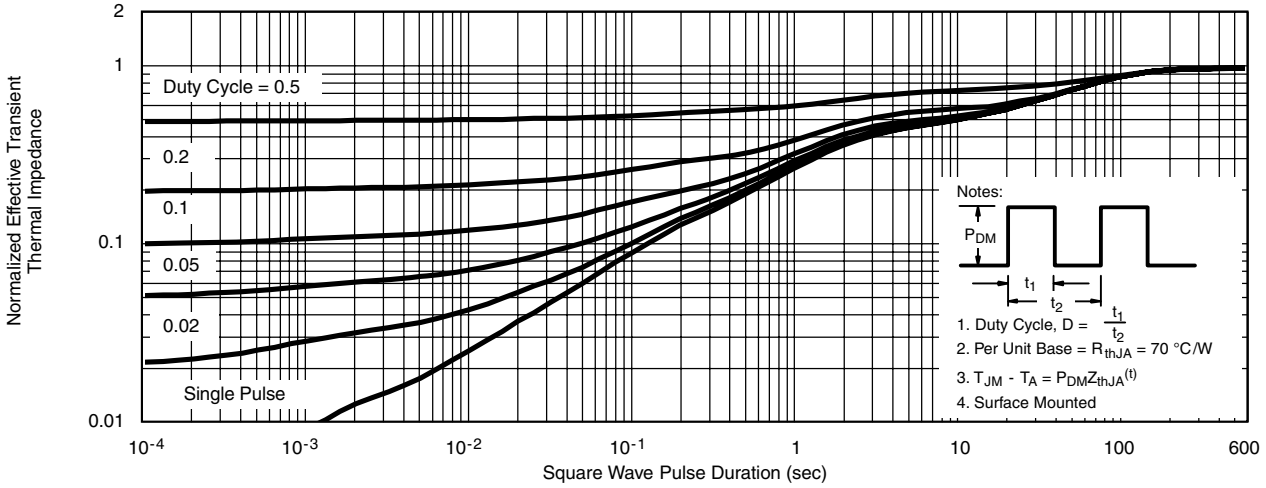


Single Pulse Power, Junction-to-Ambient

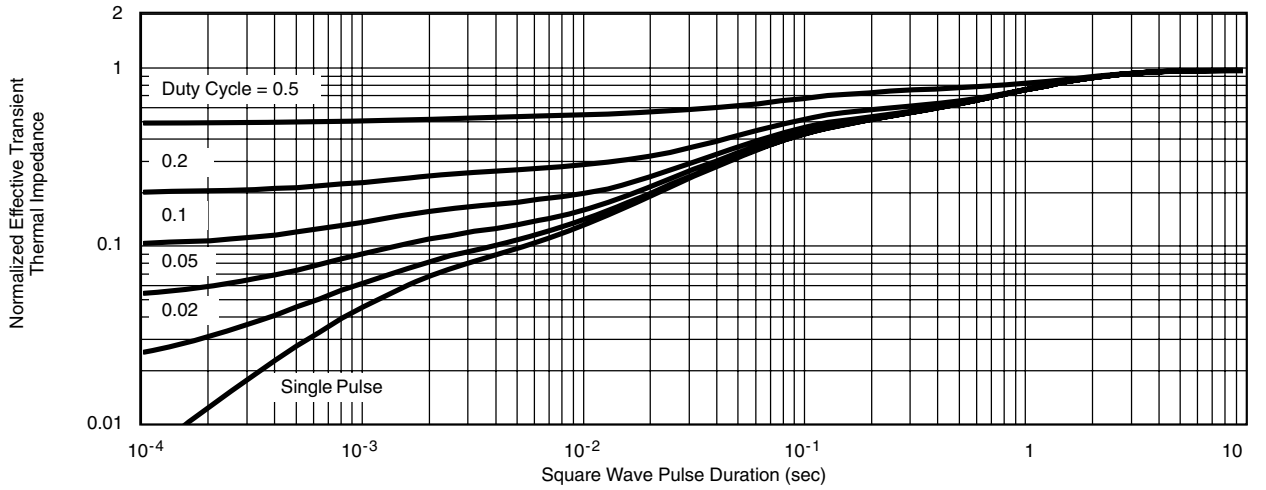


Safe Operating Area

TYPICAL CHARACTERISTICS 25 °C, unless noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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